

SANYO	No.3761A	2SJ188
	P-Channel MOS Silicon FET	
Very High-Speed Switching Applications		

Features

- Low ON resistance
- Very high-speed switching
- Low-voltage drive

Absolute Maximum Ratings at Ta = 25°C

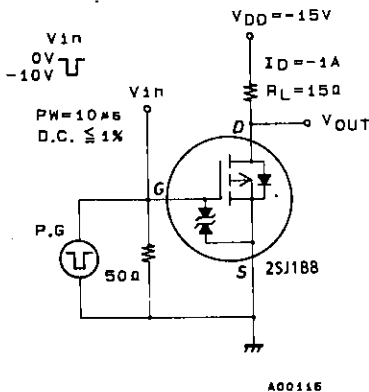
			unit
Drain to Source Voltage	V _{DSS}	-30	V
Gate to Source Voltage	V _{GSS}	±15	V
Drain Current (DC)	I _D	-2	A
Drain Current (Pulse)	I _{DP}	-8	A
Allowable Power Dissipation	P _D	20	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

PW ≤ 10 μs, duty cycle ≤ 1%
T_c = 25°C

Electrical Characteristics at Ta = 25°C

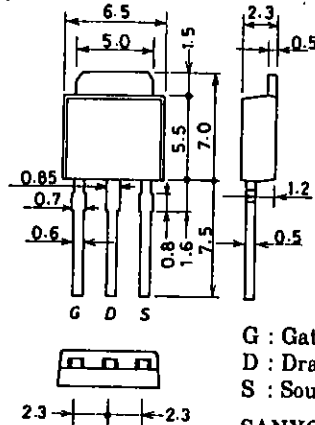
			min	typ	max	unit
D-S Breakdown Voltage	V _{(BR)DSS}	I _D = -1mA, V _{GS} = 0	-30			V
G-S Breakdown Voltage	V _{(BR)GSS}	I _G = ±100 μA, V _{DS} = 0	±15			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -30V, V _{GS} = 0			-100	μA
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±12V, V _{DS} = 0			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} = -10V, I _D = -1mA	-1.0		-2.0	V
Forward Transfer Admittance	Y _{fs}	V _{DS} = -10V, I _D = -1A	1.2	2		S
Static Drain to Source on State Resistance	R _{DSON}	I _D = -1A, V _{GS} = -10V		0.2	0.3	Ω
	R _{DSON}	I _D = -1A, V _{GS} = -4V		0.3	0.45	Ω
Input Capacitance	C _{iss}	V _{DS} = -10V, f = 1MHz		400		pF
Output Capacitance	C _{oss}	V _{DS} = -10V, f = 1MHz		280		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} = -10V, f = 1MHz		110		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit		12		ns
Rise Time	t _r	∕		25		ns
Turn-OFF Delay Time	t _{d(off)}	∕		105		ns
Fall Time	t _f	∕		75		ns
Diode Forward Voltage	V _{SD}	I _S = -2A, V _{GS} = 0	-1.0	-1.5		V

Switching Time Test Circuit



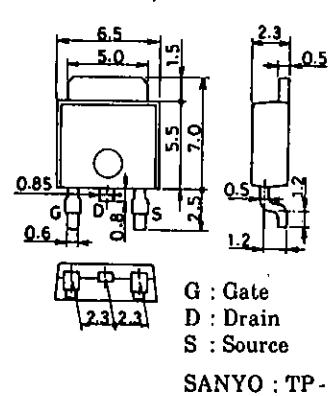
Package Dimensions 2083A

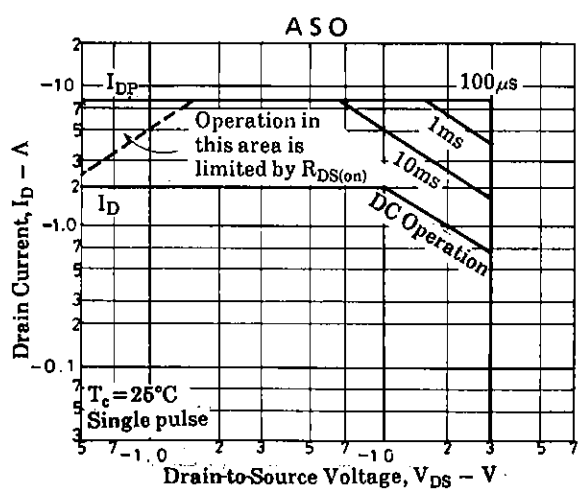
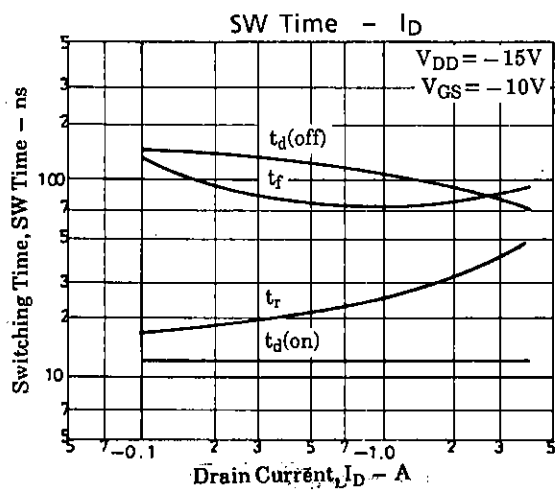
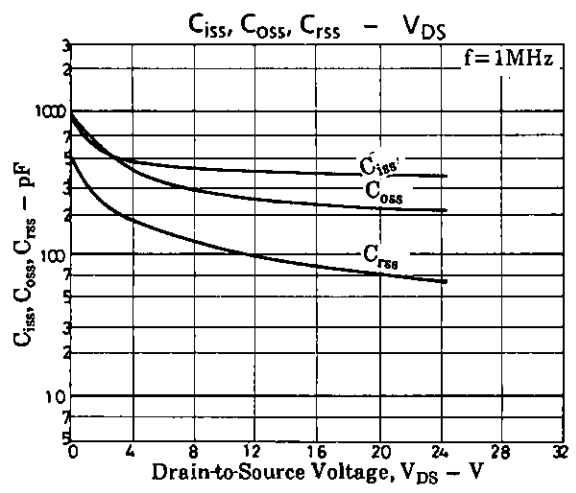
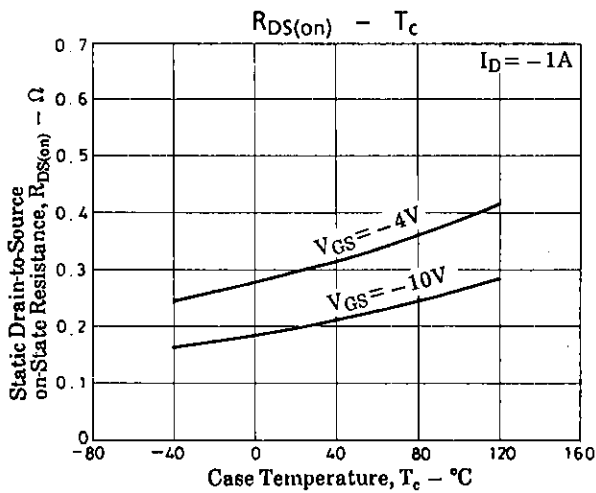
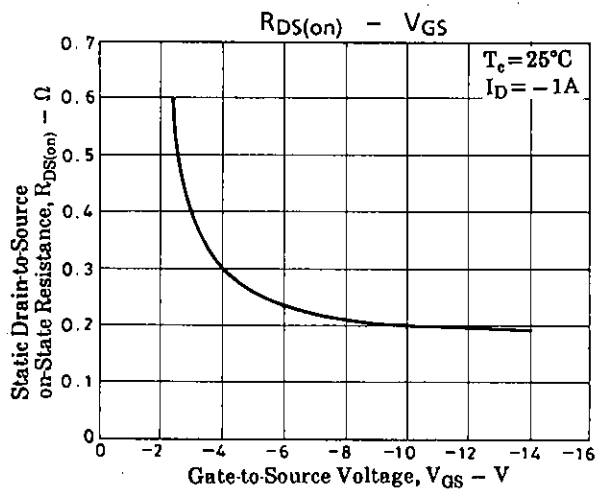
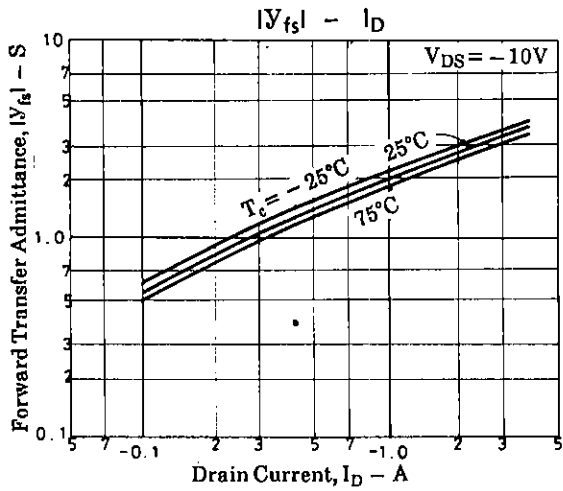
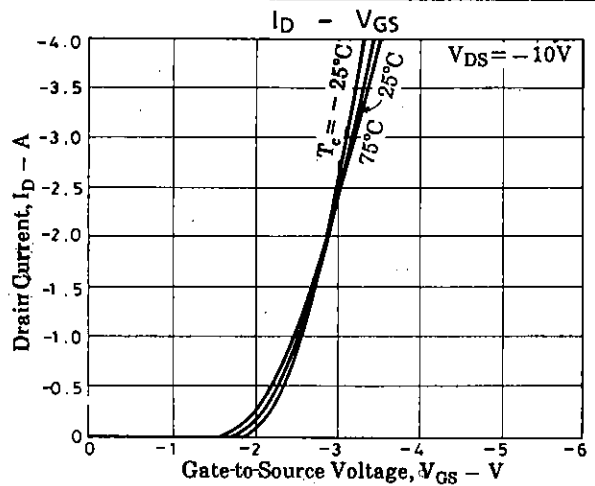
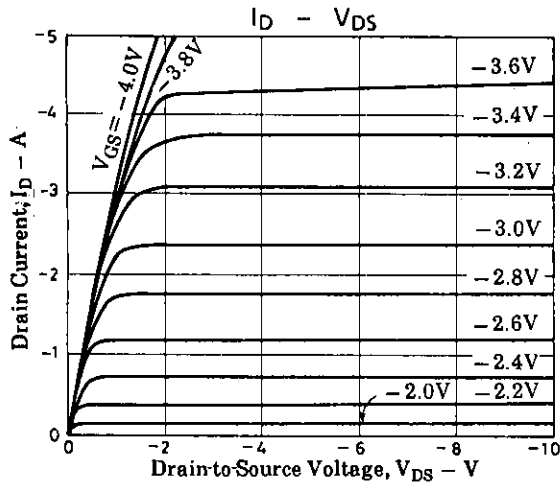
(unit: mm)

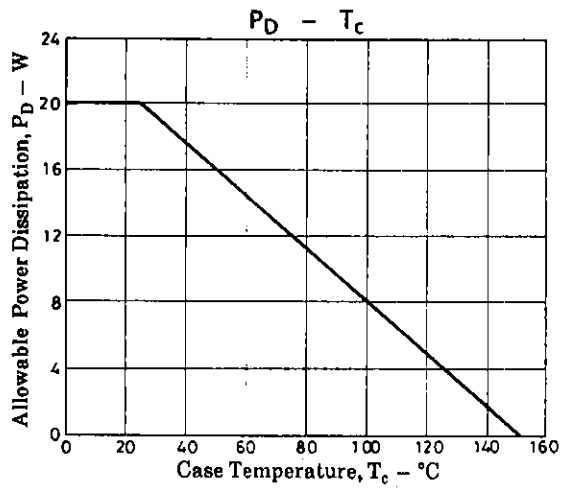


Package Dimensions 2092A

(unit: mm)







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